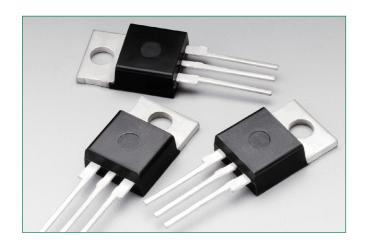
# 2N6504 Series

Surface Mount - 50 - 800V





#### **Description**

The 2N6504 is designed primarily for half-wave AC control applications, such as motor controls, heating controls and power supply crowbar circuits.

#### **Features**

- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- 300 A Surge Current Capability
- Pb-Free Package is Available

#### **Additional Information**



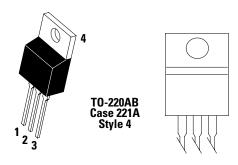




**Functional Diagram** 



#### **Pin Out**









**Samples** 

## **Maximum Ratings** (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, T <sub>J</sub> = 25 to 125°C)  2N6507 2N6507 2N6508 2N6509		$egin{array}{c} V_{ m DRM'} \ V_{ m RRM} \end{array}$	50 100 400 600 800	V
On-State RMS Current (180° Conduction Angles; $T_c = 85$ °C	I <sub>T (RMS)</sub>	25	Α	
Average On-State Current (180° Conduction Angles; $T_c = 88$	I <sub>T (AV)</sub>	16	А	
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T <sub>J</sub> = 100°C)	I <sub>TSM</sub>	250	А	
Forward Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ s, T $_{\rm C}$ = 85°C)	$P_{GM}$	20	W	
Forward Average Gate Power (t = $8.3 \text{ ms}$ , $T_{c} = 85^{\circ}\text{C}$ )	$P_{G(AV)}$	0.5	W	
Forward Peak Gate Current (Pulse Width $\leq 1.0 \mu s$ , $T_{\rm C} = 85^{\circ} {\rm C}$	I <sub>GM</sub>	2.0	А	
Operating Junction Temperature Range	T <sub>J</sub>	-40 to +125	°C	
Storage Temperature Range	$T_{stg}$	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

#### **Thermal Characteristics**

Rating	Symbol	Value	Unit
*Thermal Resistance, Junction to Case	R <sub>eJC</sub>	1.5	°C/W
*Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T <sub>L</sub>	260	°C

<sup>\*</sup> Indicates JEDEC Registered Data.

#### **Electrical Characteristics - OFF** (TC = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
†Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	10	μΑ
$(V_{AK} = V_{DRM} = V_{RRM}; Gate Open)$	T <sub>J</sub> = 125°C	IRRM	-	-	2.0	mA

# **Electrical Characteristics - ON** (TC = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
* Forward On-State Voltage (Note 2) (ITM = 50 A)		$V_{TM}$	_	_	1.8	V
* Gate Trigger Current (Continuous dc)	$T_{c} = 25^{\circ}C$	ı	_	9.0	30	^
* Gate Trigger Current (Continuous dc) $T_{\rm C} = 25^{\circ}{\rm C}$ $(V_{\rm AK} = 12V_{\rm dc},  {\rm RL} = 100)$ $T_{\rm C} = -40^{\circ}{\rm C}$		GT	_	_	75	mA
* Gate Trigger Voltage (Continuous dc) ( $V_{AK} = 12 \text{ Vdc}, R_{L} = 100 \text{ C}$	$\Omega \Omega$ , $T_{c} = -40  ^{\circ}C$	$V_{GT}$	_	1.0	1.5	V
Gate Non-Trigger Voltage ( $V_{AK} = 12 \text{ Vdc}$ , $R_{L} = 100 \Omega$ , $T_{J} = 125 ^{\circ}\text{C}$ )		$V_{GD}$	0.2	_	_	V
*Holding Current ( $V_D = 12 \text{ Vdc}$ , $T_C = 25^{\circ}\text{C}$		1	-	18	40	mA
Initiating Current = 200 mA, Gate Open) $T_c = -40$ °C		Ч	-	-	80	IIIA
* Turn-On Time ( $I_{TM} = 25 \text{ A}, I_{GT} = 50 \text{ mAdc}$ )		t <sub>gt</sub>	-	-	-	μs
Turn-Off Time ( $V_{RM}$ = rated voltage) ( $I_{TM}$ = 25 A, $I_{R}$ = 25 A)		t <sub>q</sub>	-	-	-	μs

<sup>\*</sup>Indicates JEDEC Registered Data

<sup>2.</sup> Pulse Test: Pulse Width ≤ 300 µsec, Duty Cycle ≤ 2%.



Recommended Operating Conditions may affect device reliability.

1. V<sub>DBM</sub> and V<sub>SBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

# **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Off-State Voltage (Gate Open, Rated VDRM, Exponential Waveform)	dv/dt(c)	-	50	_	V/µs

# **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
l <sub>u</sub>	Holding Current

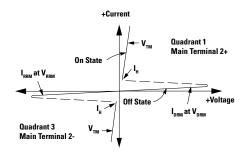


Figure 1. AverageCurrent Derating

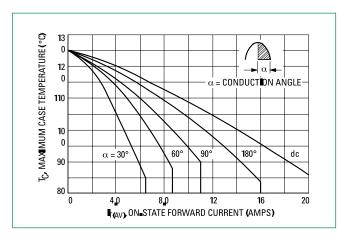


Figure 2. Maximum On-State Power Dissipation

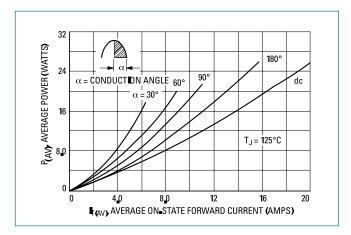


Figure 3. Typical On-State Characteristics

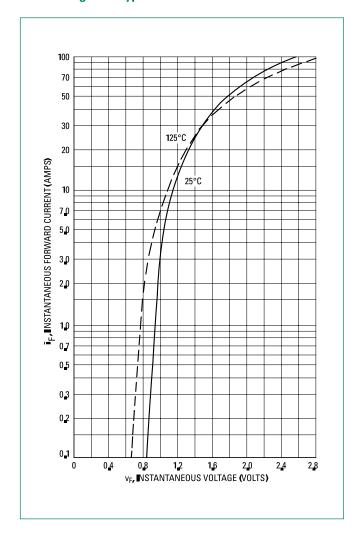


Figure 4. Maximum Non-Repetitive Surge Current

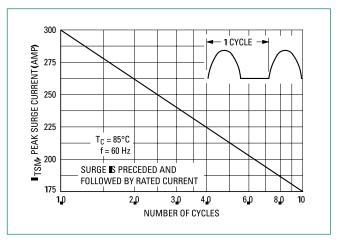
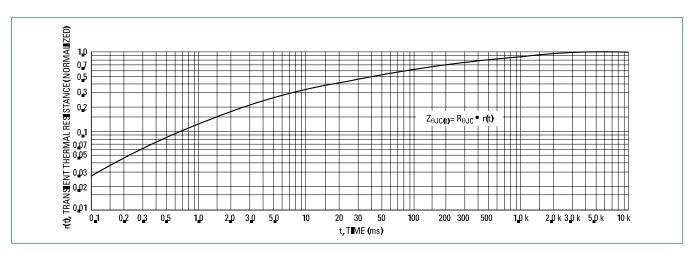


Figure 5. Thermal Response





# **Typical Trigger Characteristics**

Figure 6. Typical Gate Trigger Current vs. Junction Temperature

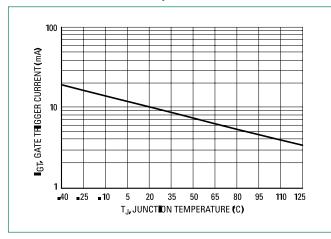


Figure 8. Typical Holding Current vs. Junction Temperature

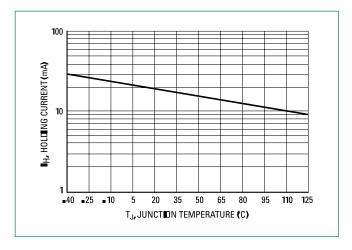
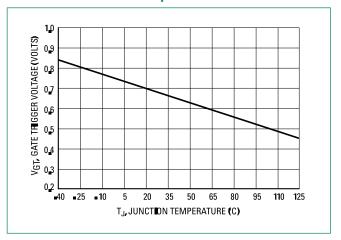


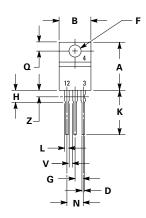
Figure 7. Typical Gate Trigger Voltage vs. Junction Temperature

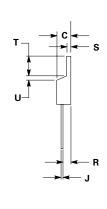


# 2N6504 Series

Surface Mount - 50 - 800V

#### **Dimensions**

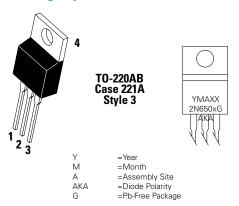




D.	Inches		Millim	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

- Dimensioning and tolerancing per ansi γ14.5m, 1982.
   Controlling dimension: inch.
   Dimension z defines a zone where all body and lead irregularities are allowed.

## **Part Marking System**



Pin Assignment			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

# **Ordering Information**

Device	Package	Shipping
2N6504	TO-220AB	
2N6504G	TO-220AB (Pb-Free)	1000 Units / Box
2N6505	TO-220AB	1000 Offits / Box
2N6505G	TO-220AB (Pb-Free)	
2N6505T	TO-220AB	
2N6505TG	TO-220AB (Pb-Free)	1000 Units / Box
2N6507	TO-220AB	
2N6507G	TO-220AB (Pb-Free)	1000 Units / Box
2N6507T	TO-220AB	
2N6507TG	TO-220AB (Pb-Free)	1000 Units / Box
2N6508	TO-220AB	
2N6508G	TO-220AB (Pb-Free)	1000 Units / Box
2N6508TG	TO-220AB	1000 Units / Box
2N6509	TO-220AB (Pb-Free)	1000 Units / Box
2N6509G	TO-220AB	
2N6509T	TO-220AB (Pb-Free)	1000 Units / Box
2N6509TG	TO-220AB	

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